

IN THE SPECIFICATION

On page 6, please amend paragraph 0027 as follows between the dashes.

—In manufacturing the P2 structure, the method according to the invention is used to stamp the necessary critical dimension geometry into the resist layer on top of the planarized layer, in the present case the write gap. In order to achieve ~~Anna Maria Petrona Markham/IBM@IBMC~~ an appropriate throughput, a multiple stamp array, like, e.g., a flash field, can be used. According to the invention, a P2 structure or microstructure having an aspect ratio in a range of 1:5 to 1:20 is achievable.--

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